

Term	Plaintiff's Proposed Construction	Defendants' Proposed Construction	Court's Preliminary Construction
“a second, thicker oxide layer” / “a gate oxide layer” U.S. Patent No. 8,035,112, Cls. 1, 6	“layer of oxide that is on the tops and sides of each gate and that is thicker than the layer of oxide below each gate”	“an oxidation layer formed, created, or grown by reacting the gate, thicker than the first oxide layer”	Plain-and-ordinary meaning
“double-implanted metal-oxide semiconductor field effect transistor” U.S. Patent No. 7,498,633, Cl. 9	The preamble is not limiting. In the alternative only, “double-implanted” is not limiting. ¹	The preamble is limiting.	The preamble is limiting.
“less than about three micrometers” U.S. Patent No. 7,498,633, Cl. 9	Plain and ordinary meaning, no construction necessary.	Indefinite	Not indefinite. Plain-and-ordinary meaning.

¹ ST notes that Purdue previously offered that “[i]n the alternative only, ‘metal-oxide semiconductor field-effect transistor is limiting.’”